

N沟道增强型场效应晶体管/N-CHANNEL MOSFET

●特点：■低栅极电荷 ■低Crss ■开关速度快 ■符合ROHS规范

●FEATURES: ■LOW GATE CHARGE ■LOW Crss ■FAST SWITCHING ■ROHS COMPLIANT

●应用 ■高频开关电源 ■电子镇流器等开关电路

●APPLICATION: ■High efficiency switch mode power supplies ■Electronic ballast ECT.

●绝对最大额定值 (TC=25°C)

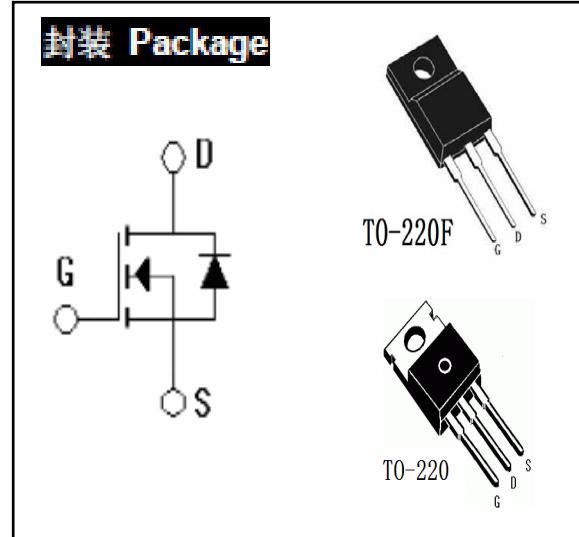
●Absolute Maximum Ratings (TC=25°C)

参数名称 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
漏极-源极电压 Drain-Source Voltage	VDSS	650	V
连续漏极电流 Drain Current-continuous	ID	12	A
最大脉冲漏极电流 Drain Current-pulse	IDM	48	A
最高栅源电压 Gate-Source Voltage	VGSS	±30	V
耗散功率 Power Dissipation	PD	51	W
最高结温 Junction Temperature	Tj	150	°C
贮存温度 Storage Temperature	Tstg	-55-150	°C

电特性 (TC=25°C)

Electronic Characteristics(Tc=25°C)

参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	典型值 Typ	最大值 MAX	单位 UNIT
漏极-源极击穿电压 Drain-Source Voltage	BVDSS	ID=250uA;VGS=0V	650			V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	IDSS	VDS=650V,VGS=0V (TC=25°C)			1.0	uA
正向栅极体漏电流 Gate-body leakage current.forward	IGSSF	VDS=0V,VGS=30V			100	nA
反向栅极体漏电流 Gate-body leakage current.reverse	IGSSR	VDS=0V,VGS=-30V			-100	nA
阈值电压 Gate Threshold Voltage	VGS(th)	VDS=VGS,ID=250uA	3.0		5.0	V
静态导通电阻 Static Drain-Source On-Resistance	RDS(ON)	VGS=10V, ID=6 A		0.71	0.78	Ω
正向跨导 Forward Transconductance	Gfs	VDS=40V, ID=6 A		13		S
输入电容 Input capacitance	Ciss	VDS=25V VGS=0V f=1.0MHZ		1790	2401	pF
输出电容 Output capacitance	Coss			175	229	pF
反向传输电容 Reverse transfer capacitance	Crss			23	31	pF



电特性

Electronic Characteristics

单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy	EAS	880.0	MJ
雪崩电流 (注1) Avalanche Current (注 1)	IAR	12	A
重复雪崩能量 (注1) Repetitive Avalanche Current (note1)	EAR	25	MJ
二极管反向恢复最大电压变化速率 (注3) Peak Diode Recovery dv/dt(note 3)	dv/dt	4.5	v/ns

开关特征 Switching Characteristics

延迟时间 Turn-On delay time	td(on)	$V_{DD}=300V, I_D=12A, R_G=25\Omega$ (注4, 5)	-	78	102	ns
上升时间 Turn-On rise time	tf		-	133	175	ns
延迟时间 Turn-Off delay time	td(off)		-	233	305	ns
下降时间 Turn-Off rise time	tf		-	104	160	ns
栅极电荷总量 Total Gate Charge	Qg	$V_{DS}=480V, I_D=12A, V_{GS}=10V$ (注4, 5)	-	39	52	nc
栅-源电荷 Gate-Source charge	Qgs		-	8.5	-	nc
栅-漏电荷 Gate-Drain charge	Qgd		-	20	-	nc

漏-源二级管特征及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings

正向最大连续电流 Maximum continuous Drain-Source Diode Forward Current	I_S		-	-	12	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	48	A
正向压降 Drain-Source Diode Forward Voltage	V_{SDF}	$V_{GS}=0V, I_S=12.0A$	-	-	1.39	V
反向恢复时间 Reverse recovery time	Tr _r	$V_{GS}=0V, I_S=12.0A$ $dI/F/dt=100A/us$ (note 4)	-	418	-	ns
反向恢复电荷 Reverse recovery charge	Q _{rr}		-	4.85	-	μC

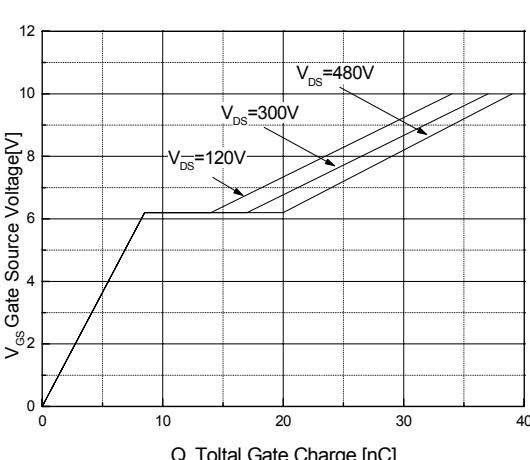
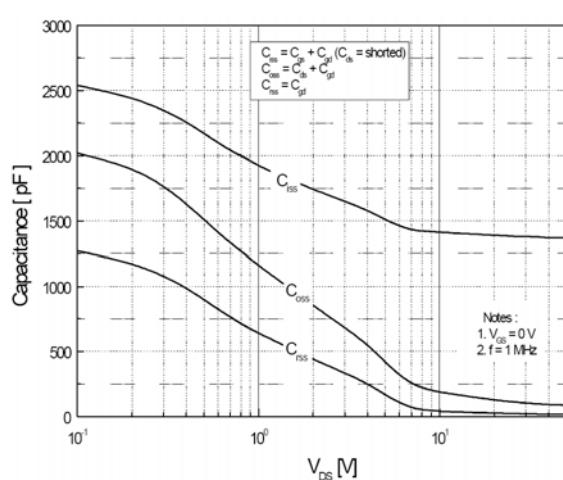
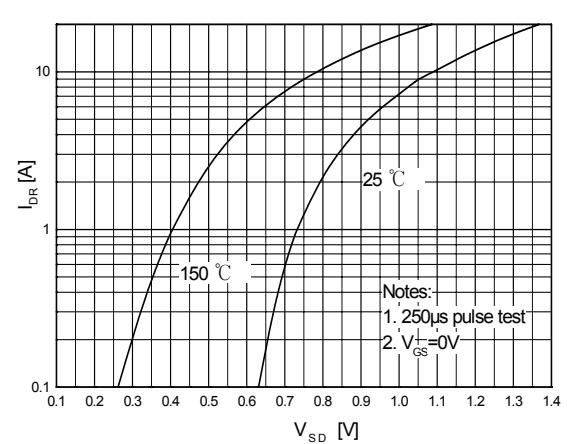
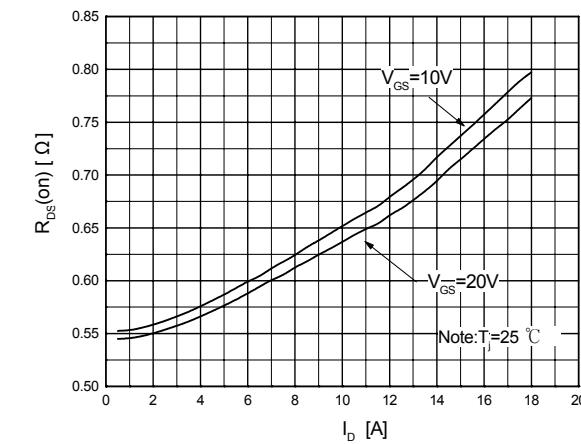
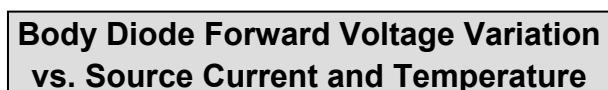
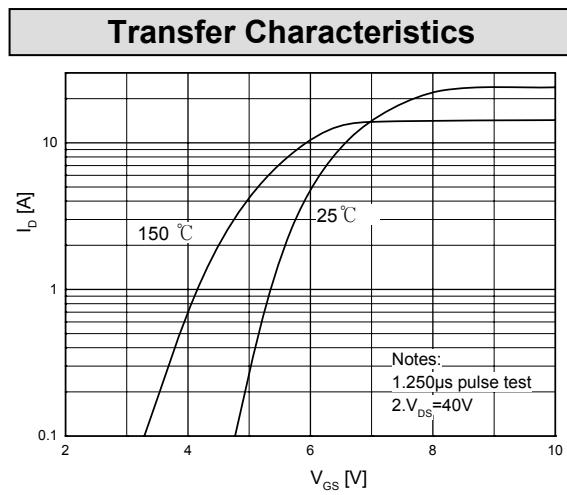
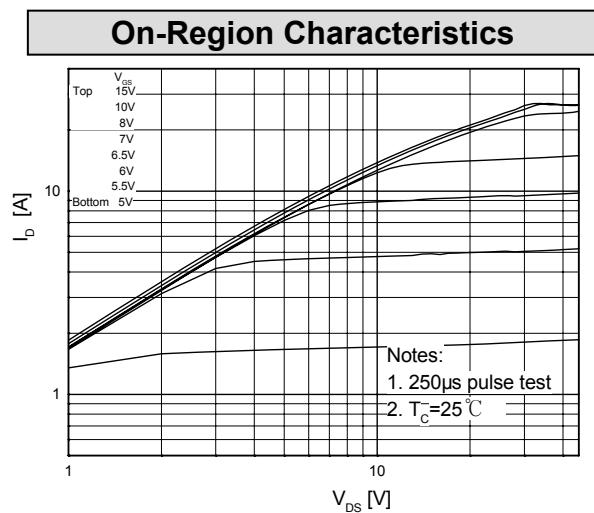
热特征 Thermal Characteristic

项目 Parameter	符号 Symbol	最大 (Max)		单位 Unit
		T0-220(铁封)	T0-220F塑封	
结到管壳的热阻 Thermal Resistance, Junction to case	R _{th(j-c)}	0.5	2.45	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	R _{th(j-a)}	62.5	62.5	°C/W

注释:

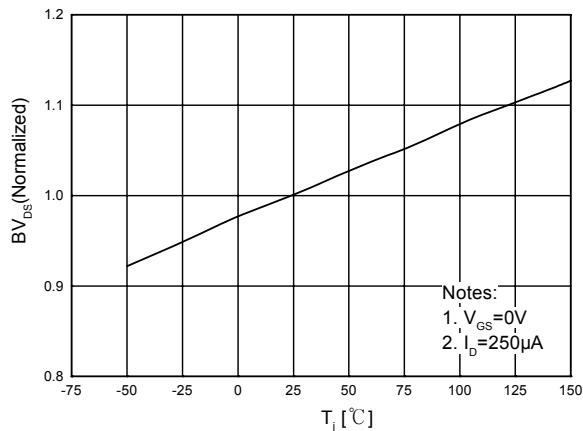
- 1、脉冲宽度由最高结温限制
- 2、L=14.5mH, IAS=12.0, VDD=50V, RG=25Ω, 起始结温T_j=25°C
- 3、ISO 《12.0A, di /dt 《300A/us, VDD 《BVDSS, 起始结温T_j =25°C
- 4、脉冲测试：脉冲宽度《300us, 占空比《2%
- 5、基本与工作温度无关

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

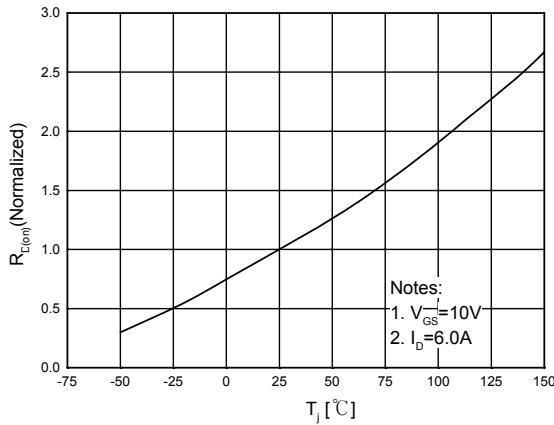


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

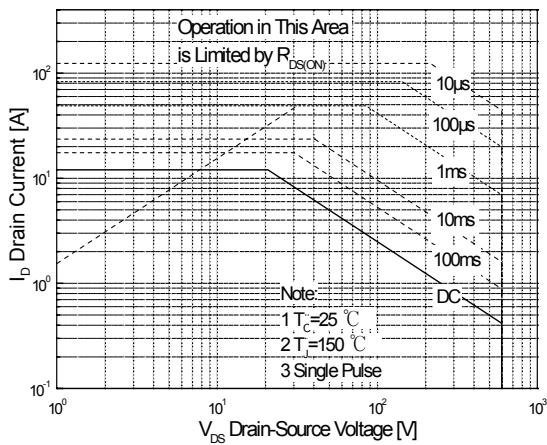
Breakdown Voltage Variation vs. Temperature



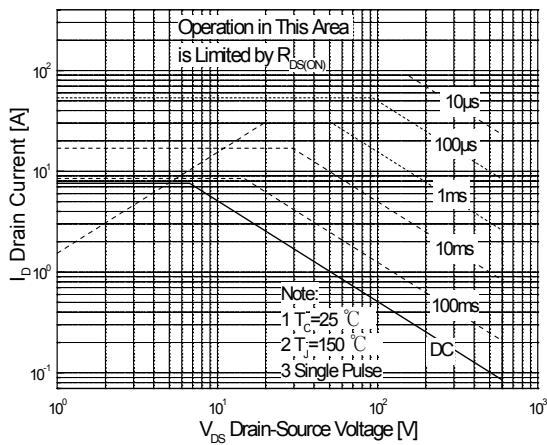
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area For TO-220



Maximum Safe Operating Area For TO-220F



Maximum Drain Current vs. Case Temperature

